

BYW99P/PI/W**THERMAL RESISTANCES**

Symbol	Parameter			Value	Unit
Rth (j-c)	Junction to case	SOT93 / TO247	Per diode	1.8	°C/W
			Total	1.0	
		TOP3I	Per diode	2.0	
			Total	1.25	
Rth (c)	Coupling	SOT93 / TO247		0.2	°C/W
		TOP3I		0.5	

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			20	μA
	T _j = 100°C				1.5	mA
V _F **	T _j = 125°C	I _F = 12 A			0.85	V
	T _j = 125°C	I _F = 25 A			1.05	
	T _j = 25°C	I _F = 25 A			1.15	

Pulse test : * t_p = 50 ns, δ < 2 %

** t_p = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.55 \times I_{F(AV)} + 0.016 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A I _R = 1A			25	ns
		I _F = 1A V _R = 30V			40	
tfr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 x V _F		15		ns
V _{FP}	T _j = 25°C	I _F = 1A tr = 10 ns		2		V

Fig.1 : Average forward power dissipation versus average forward current.

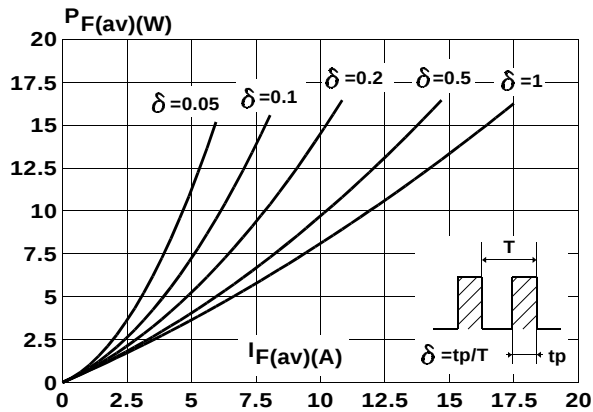


Fig.2 : Peak current versus form factor.

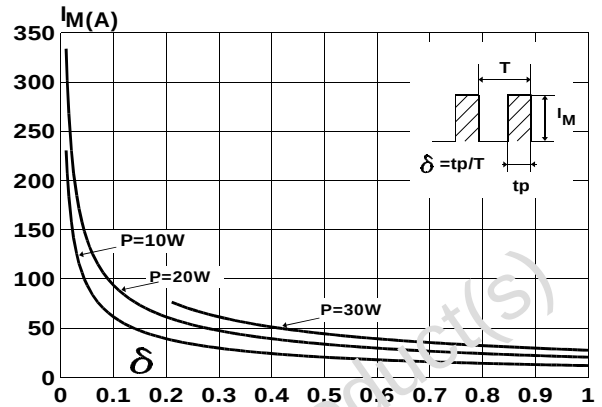


Fig.3 : Forward voltage drop versus forward current (maximum values).

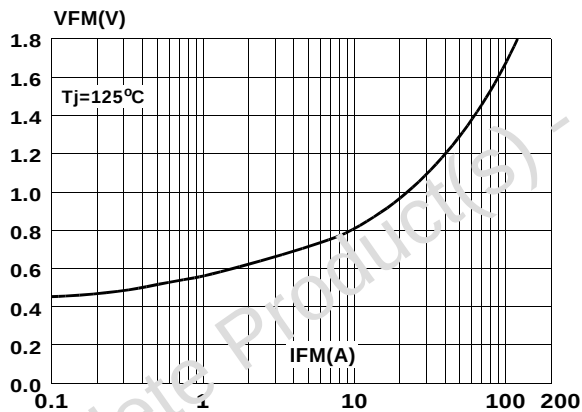


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

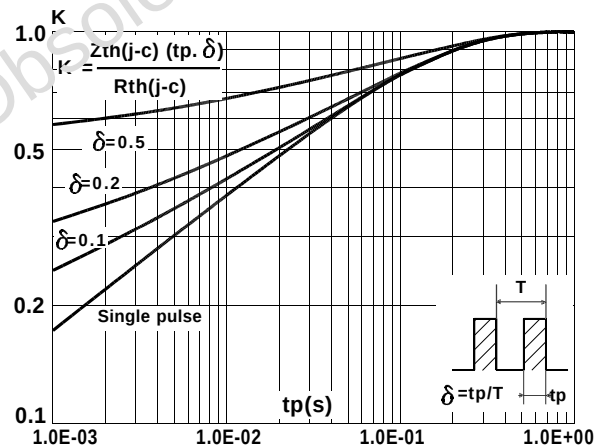


Fig.5 : Non repetitive surge peak forward current versus overload duration. (SOT93, TO247)

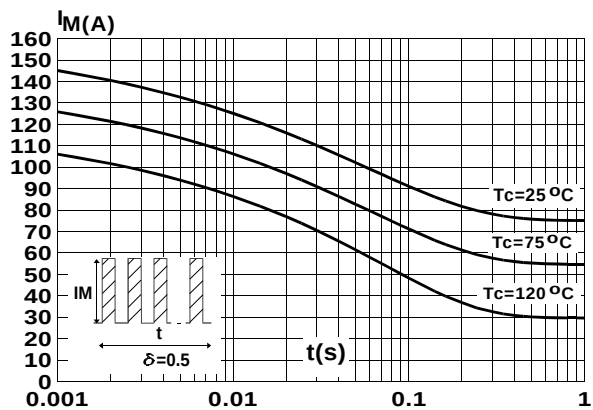


Fig.6 : Non repetitive surge peak forward current versus overload duration. (TOP3I)

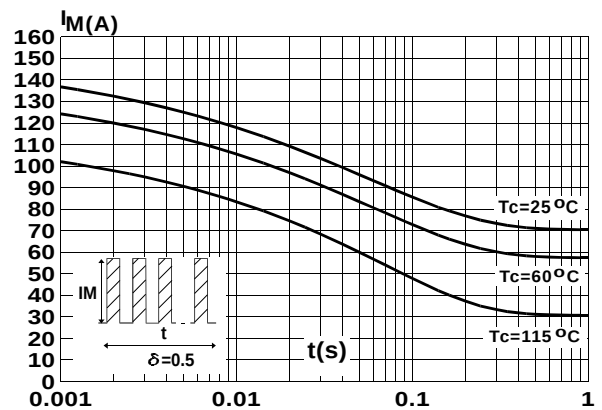


Fig.7 : Average current versus ambient temperature.
($\delta = 0.5$) (SOT93, TO247)

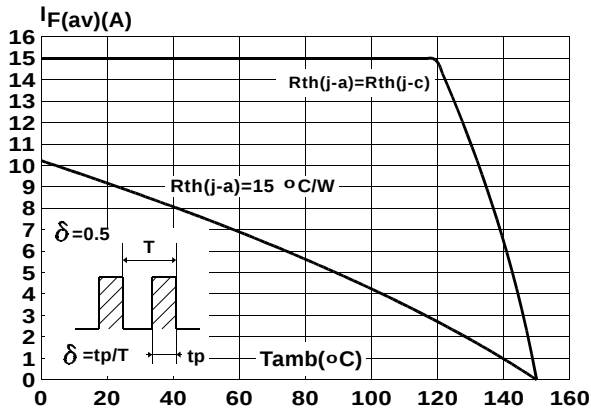


Fig.8 : Average current versus ambient temperature.
($\delta = 0.5$) (TOP3I)

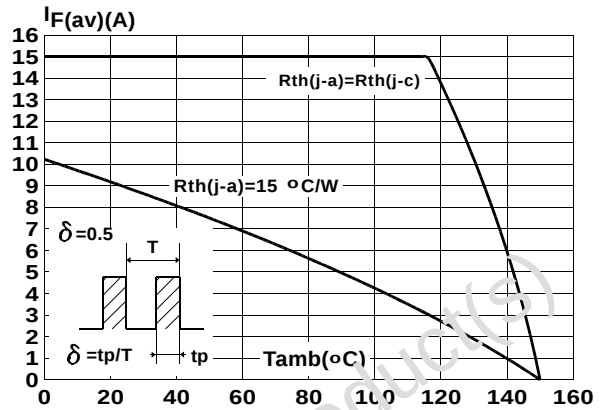


Fig.9 : Junction capacitance versus reverse voltage applied (Typical values).

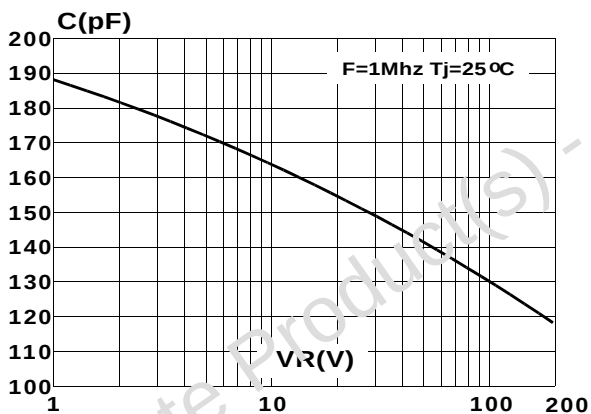


Fig.10 : Recovery charges versus dI_F/dt .

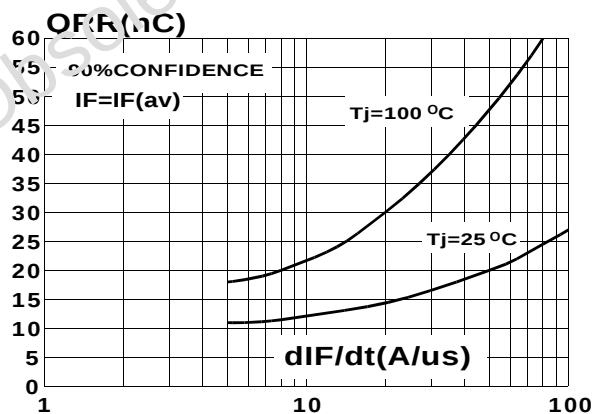


Fig.11 : Peak reverse current versus dI_F/dt .

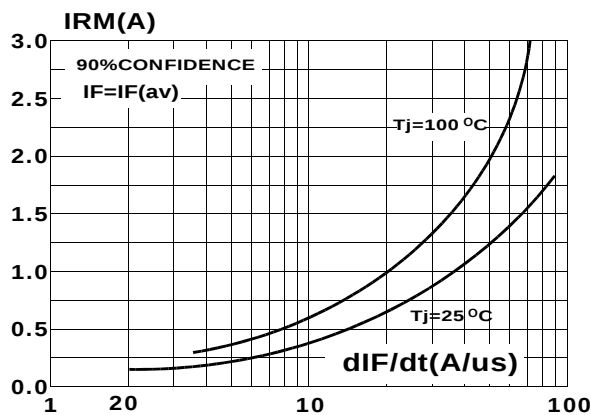
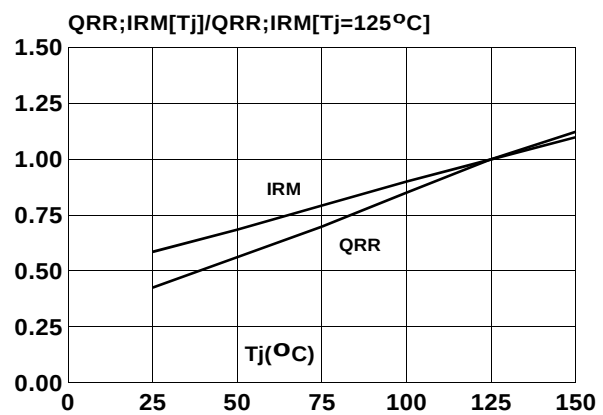
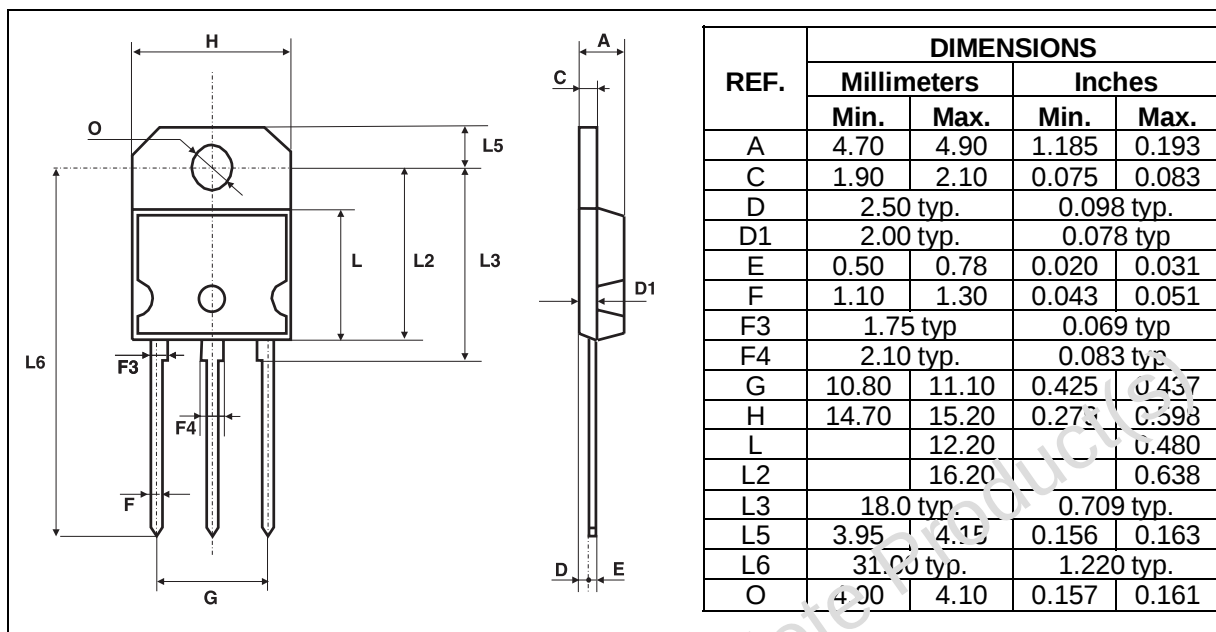


Fig.12 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA

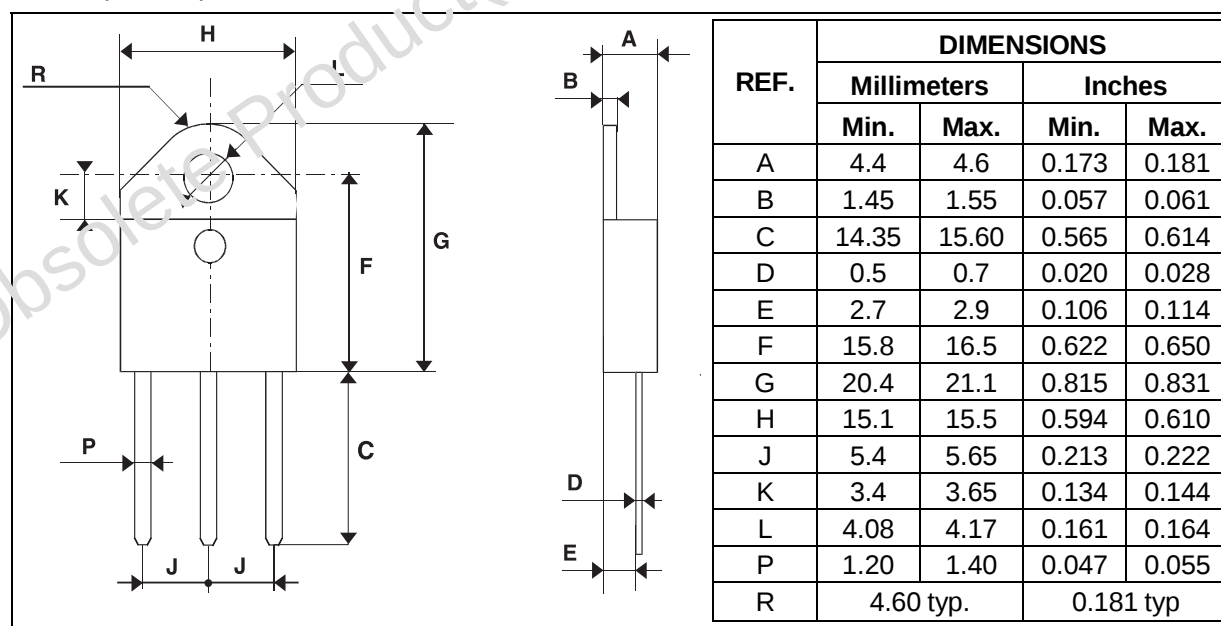
SOT93



- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 5.3 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N

PACKAGE MECHANICAL DATA

TOP3I (isolated)

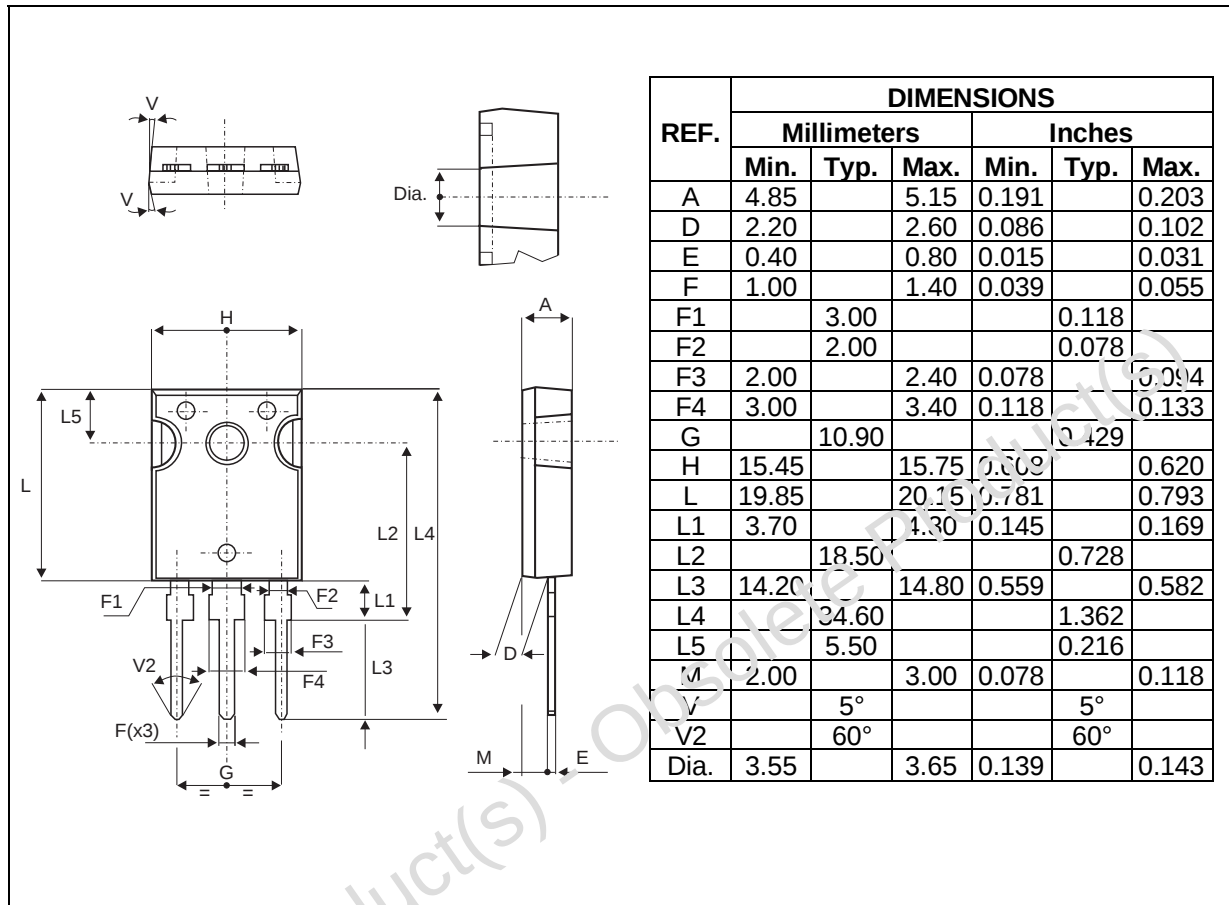


- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 4.7 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N



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PACKAGE MECHANICAL DATA TO247



- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 4.4 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N

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